AMENDMENTS TO THE SPECIFICATION

Kindly replace the title with the following amended title:

METAL INTERCONNECTION WITH LOW RESISTANCE IN A SEMICONDUCTOR DEVICE ~~AND A METHOD OF FORMING THE SAME~~

Kindly replace the first paragraph of the specification with the following amended first paragraph:

This application is a division of application Serial No. 10/134,748, filed April 30, 2002, now U.S. Patent No. 6,670,268.

Kindly replace paragraph [0032] with the following amended paragraph:

[0032] In addition, an embodiment of the present invention provides an advanced structure of metal interconnection for a semiconductor device, including an inter-layer insulation film formed on a semiconductor substrate, containing a bit line contact hole, a plug formed in the contact hole, and a bit line including a bit line barrier metal defined on the plug within the contact hole, and a bit line metal film formed directly on the bit line barrier metal and the inter-layer insulation film.

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Kindly replace paragraph [0034] with the following amended paragraph:

[0034] Another feature of an embodiment of the present invention referring to a metal interconnection structure of a semiconductor device includes an inter-layer insulation film formed on a semiconductor substrate containing a bit line contact hole; a plug partially filling the contact hole, a bit line barrier metal defined on the plug and filling the rest of the contact hole; and a bit line metal film of a bit line formed on the bit line barrier metal and the inter-layer insulation film.

Kindly replace paragraph [0035] with the following amended paragraph:

[0035] Still another feature of an embodiment of the present invention referring to a metal interconnection structure of a semiconductor device includes an inter-layer insulation film formed on a semiconductor substrate containing a bit line contact hole; a plug completely filling the contact hole; a bit line barrier metal defined on the plug in the contact hole; and a bit line metal film of a bit line formed directly on the bit line barrier metal and the inter-layer insulation film.

Kindly cancel the Abstract of the Disclosure and replace the Abstract of the Disclosure with a new Abstract of the Disclosure, which is attached hereto at page 17.

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